LL101A...LL101C

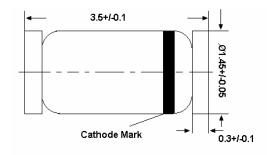
SILICON SCHOTTKY BARRIER DIODES

for general purpose applications

The LL101 Series is a metal on silicon Schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications.

This diode is also available in DO-35 case with type designation

SD101A, B, C.



Glass case MiniMELF Dimensions in mm

Absolute Maximum Ratings $(T_a = 25^{\circ}C)$

		Symbol	Value	Unit	
Peak Reverse Voltage	LL101A	V_{RRM}	60	V	
	LL101B	V_{RRM}	50	V	
	LL101C	V_{RRM}	40	V	
Power Dissipation (Infinite Heatsink)		P _{tot}	400 ¹⁾	mW	
Max. Single Cycle Surge		I	2	Α	
10μs Squarewave		I _{FSM}	۷		
Junction Temperature		Tj	200	°C	
Storage Temperature Range		T _S	-55 to +200	оС	
1) Valid provided that electrodes are kept at amb	pient temperature.				









LL101A...LL101C

Characteristics at T_{amb} = 25°C

		Symbol	Min.	Тур.	Max.	Unit
Reverse Breakdown Voltage						
at $I_R = 10\mu A$	LL101A	$V_{(BR)R}$	60	-	-	V
	LL101B	$V_{(BR)R}$	50	-	-	V
	LL101C	$V_{(BR)R}$	40	-	-	V
Forward Voltage Drop						
at I _F = 1mA	LL101A	V_{F}	_	_	0.41	V
	LL101B	V _F	_	-	0.4	V
	LL101C	V _F	-	-	0.39	V
at I _F = 15mA	LL101A	V _F	-	-	1	V
	LL101B	V_{F}	-	-	0.95	V
	LL101C	V_{F}	-	-	0.9	V
Leakage Current						
at $V_R = 50V$	LL101A	I _R	-	-	200	nA
at $V_R = 40V$	LL101B	I _R	-	-	200	nA
at $V_R = 30V$	LL101C	I _R	-	-	200	nA
Junction Capacitance						
at $V_R = 0V$, $f = 1MHz$	LL101A	C_{tot}	-	-	2.0	pF
	LL101B	C_{tot}	-	-	2.1	pF
	LL101C	C_{tot}	-	-	2.2	pF
Reverse Recovery Time		t	_	_	1	ns
at $I_F = I_R = 5$ mA , recover to 0.1 I_R		t _{rr}	_	_	'	113

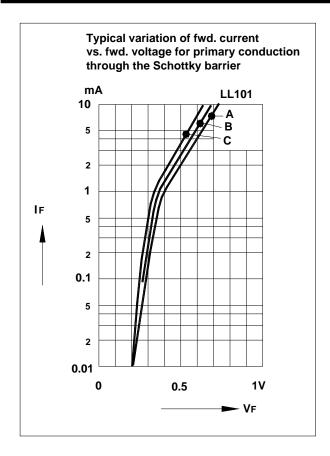


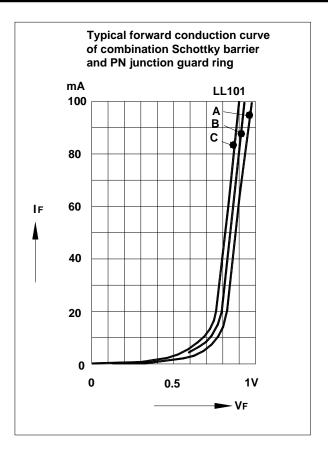


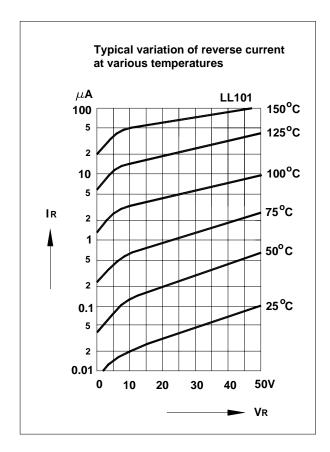


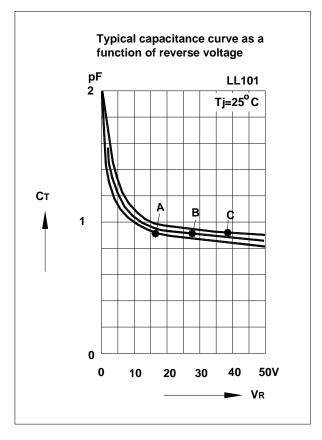


SEMTECH ELECTRONICS LTD.











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